

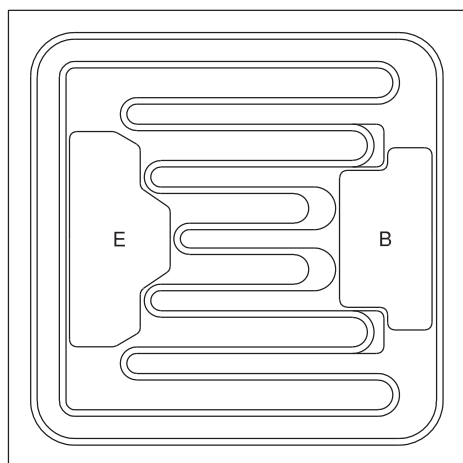
PROCESS CP305
Small Signal Transistor
NPN - High Current Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31 x 31 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.9 x 11.8 MILS
Emitter Bonding Pad Area	6.5 x 13.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R2

GROSS DIE PER 4 INCH WAFER

11,212

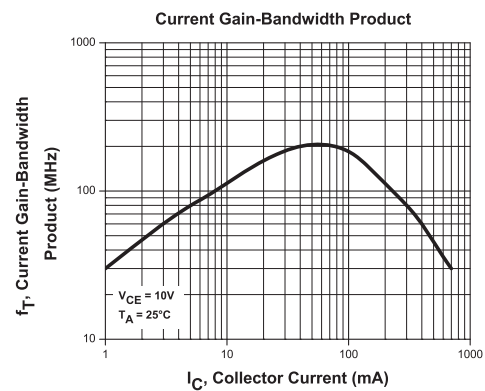
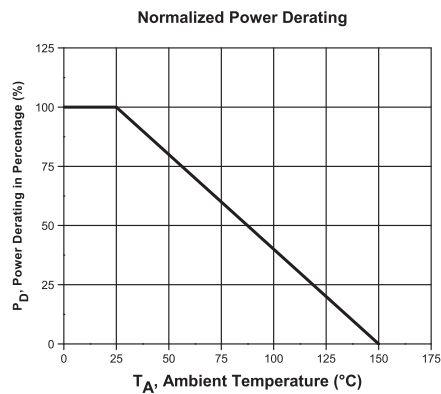
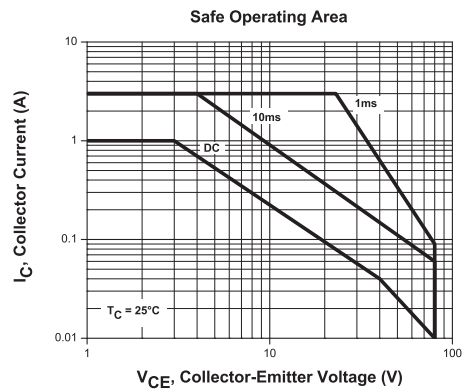
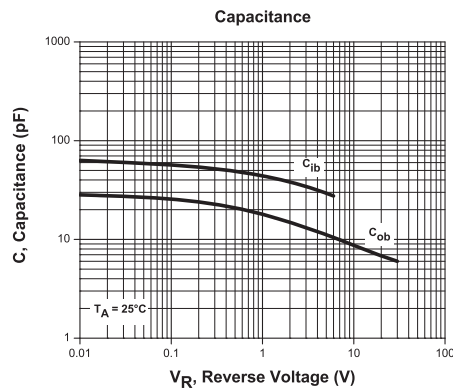
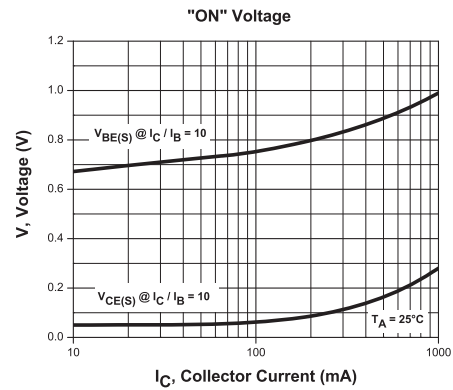
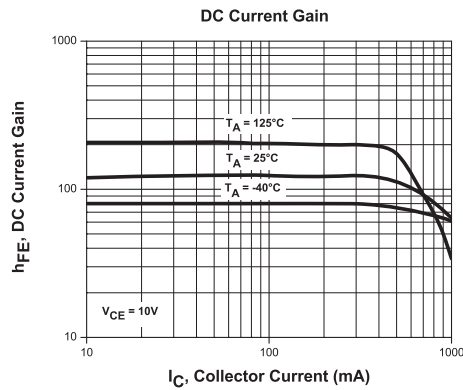
PRINCIPAL DEVICE TYPES

2N3019
CMPT3019
CXT3019
CZT3019

R3 (22-March 2010)

PROCESS CP305

Typical Electrical Characteristics



R3 (22-March 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centalsemi.com

Worldwide Field Representatives:
www.centalsemi.com/wwreps

Worldwide Distributors:
www.centalsemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centalsemi.com/terms